


PTO/SB/08A				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	09/972,608
				Filing Date	October 5, 2001
				Confirmation Number	4591
				First Named Inventor	Vladimir Voronkov et al.
				Group Art Unit	2812
				Examiner Name	Unknown
Sheet	1	of	8	Attorney Docket No.	985401/23401

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
SSS	1	4,314,595		Yamamoto et al.	02/09/1982
SSS	2	4,981,549		Yamashita et al.	01/01/1991
SSS	3	5,264,189		Yamashita et al.	11/23/1993
SSS	4	5,485,803		Habu, R.	01/23/1996
SSS	5	5,487,354		von Ammon et al.	01/30/1996
SSS	6	5,502,010		Nadahara, S. et al.	03/26/1996
SSS	7	5,667,584		Takano et al.	09/16/1997
SSS	8	5,704,973		Sakurada et al.	01/06/1998
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SSS	11	5,935,320		Graef et al.	08/10/1999
SSS	12	5,942,032		Kim et al.	08/24/1999
SSS	13	5,954,873		Hourai et al.	09/21/1999
SSS	14	5,968,262		Saishouji et al.	10/19/1999
Examiner Signature				Date Considered	12/15/2003

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SSS	15	5,968,264		Iida et al.	10/19/1999
SSS	16	6,045,610		Park et al.	04/04/2000
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SSS	20	6,228,164	B1	von Ammon et al.	05/08/2001
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T ⁶
		Office	Number ⁴	Kind Code ² (if known)			
SSS	22	EP	0 503 816	B1	Shin-Etsu Handotai Company Ltd.	09/16/1992	
SSS	23	EP	0 504 837	A2	Shin-Etsu Handotai Company Ltd.	09/23/1992	
SSS	24	EP	0 536 958	A1	Shin-Etsu Handotai Company Ltd.	04/14/1993	
SSS	25	EP	0 716 168	A1	Shin-Etsu Handotai Company Ltd.	12/06/1996	
SSS	26	EP	0 747 513	A2	Shin-Etsu Handotai Company Ltd.	12/11/1996	
SSS	27	EP	0 890 662	A1	Shinetsu Handotai KK	01/13/1999	
SSS	28	EP	0 909 840	A1	Shinetsu Handota KK	04/21/1999	

Examiner Signature	<i>Steph L. H...</i>	Date Considered	12/15/2003
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SSS	29	EP	0 962 556	A1	Shin-Etsu Handotai Company Ltd.	12/08/1999	
SSS	30	EP	0 962 557	A1	Shin-Etsu Handotai Company Ltd.	12/08/1999	
SSS	31	JP	Hei 2-180789		Kawasaki Steel Corp.	07/13/1990	X
SSS	32	JP	Hei 3-93700		Nippon Steel Corp.	04/18/1991	X
SSS	33	JP	Hei 4-108682		Fuji Electric Co., Ltd.	04/09/1992	X
SSS	34	JP	8-330316 (Pub. Hei 07-158458)		Sumitomo Sitix Corp.	12/13/1996	X
SSS	35	JP	HO 8-268794		Sumitomo Sitix Corp.	10/15/1996	X
SSS	36	JP	HO 9-202690		Shin-Etsu Semiconductor K.K.	08/05/1997	X
SSS	37	JP	11-157995	A	Sumitomo Sitix Corp.	06/15/1999	X
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SSS	39	JP	11-189495	A	Sumitomo Metal Ind. Ltd.	07/13/1999	X
SSS	40	JP	11-199386	A	Shin-Etsu Handotai Company Ltd.	07/27/1999	X
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SSS	42	PCT	WO 98/45507		MEMC Electronic Materials Inc.	10/15/1998	
SSS	43	PCT	WO 98/45508		MEMC Electronic Materials Inc.	10/15/1998	
SSS	44	PCT	WO 98/45509		MEMC Electronic Materials Inc.	10/15/1998	
SSS	45	PCT	WO 98/45510		MEMC Electronic Materials Inc.	10/15/1998	
SSS	46	PCT	WO 00/13211		MEMC Electronic Materials Inc.	03/09/2000	

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Sheet	4	of	8	Attorney Docket No.	985401/23401

SSS	47	PCT	WO 01/21861	A1	MEMC Electronic Materials Inc.	03/29/2001	
SSS	48	PCT	WO 01/21864	A1	MEMC Electronic Materials Inc.	03/29/2001	
SSS	49	PCT	WO 01/21865	A1	MEMC Electronic Materials Inc.	03/29/2001	
SSS	50	UK	GB 2 137 524	A	Hitachi Ltd. (Japan)	10/10/1984	
SSS	51	UK	GB 2 182 262	A	Sony Corp.	05/13/1987	

OTHER ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
SSS	52	ABE, T., et al., "Behavior of Point Defects in FZ Silicon Crystals", Semiconductor Silicon 1990, <i>Proceedings of the Sixth International Symposium on Silicon Materials Science and Technology</i> , Vol. 90-7 (1990), pp. 105-116	
SSS	53	ABE, T., "The formation mechanism of grown-in defects in CZ silicon crystals based on thermal gradients measured by thermocouples near growth interfaces", <i>Materials Science and Engineering</i> , Vol. B73 (2000), pp. 16-29	
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SSS	55	von AMMON, W., et al. "Bulk properties of very large diameter silicon single crystals" <i>Journal of Crystal Growth</i> , Vol. 198/199, (1999), pp. 390-398	
SSS	56	DORNBERGER, E., et al., "The Impact of Dwell Time Above 900°C During Crystal Growth on the Gate Oxide Integrity of Silicon Wafers", <i>Electrochemical Society Proceedings</i> , Vol. 96, No. 13, pp. 140-151	

Examiner Signature	<i>Steph Steen</i>	Date Considered	12/15/2003
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		Group Art Unit	2812		
		Examiner Name	Unknown		
Sheet	5	of	8	Attorney Docket No.	985401/23401

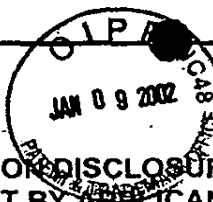
SSS	57	DORNBERGER, E., et al., "The Dependence of Ring Like Distributed Stacking Faults on the Axial Temperature Gradient of Growing Czochralski Silicon Crystals" Electrochemical Society Proceedings, Volume 95-4, (5/1995) pp. 294-305	
SSS	58	DORNBERGER, E., et al., "Simulation of Grown-In Voids in Czochralski Silicon Crystals", Electrochemical Society Proceedings, Vol. 97-22, pp. 40-49	
SSS	59	DORNBERGER, E., et al., "Simulation of Non-Uniform Grown-In Void Distributions in Czochralski Silicon Crystals", Electrochemical Society Proceedings, Vol. 98, Vol. 1, pp. 490-503	
SSS	60	EIDENZON, A.M., et al., "Defect-Free Silicon Crystals Grown By The Czochralski Technique"; Inorganic Materials, Vol. 33, No. 3, (1997) pp. 219-225.	
SSS	61	EIDENZON, A.M., et al., "Influence Of Growth Rate On Swirl Defects In Large Dislocation-Free Crystals Of Silicon Grown By The Czochralski Method", Sov. Phys. Crystallogr.; Vol. 30 , No. 5 (1985) pp. 576-580.	
SSS	62	FALSTER, R., et al., "Intrinsic Point Defects and Their Control In Silicon Crystal Growth and Wafer Processing", MRS Bulletin, Vol. 25, No. 6 (June 2000), pp.28-32	
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SSS	64	HOURAI, M., et al., "Improvement of Gate Oxide Integrity Characteristics of CZ-Grown Silicon Crystals", Progress in Semiconductor Fabrication presented by: Semiconductor Equipment and Materials International, Semicon/Europa 93, March 30-April 1, 1993, Geneva, Switzerland	
SSS	65	HOURAI, M., et al. "Growth Parameters Determining the Type of Grown-In Defects in Czochralski Silicon Crystals", Materials Science Forum, Vols. 196-201 (1995) pp. 1713-1718	
SSS	66	KISSINGER, G., et al. "A Method for Studying the Grown-In Defect Density Spectra in Czochralski Silicon Wafers" Journal of Electrochemical Society, Vol. 144, No. 4, (1997) pp. 1447-1456	

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Sheet	6	of	8	Attorney Docket No.	985401/23401

SSS	67	de KOCK, A.J.R., "The Elimination of Vacancy-Cluster Formation in Dislocation-Free Silicon Crystals", J. of the Electrochem. Soc.: SOLID-STATE SCIENCE AND TECHNOLOGY, Vol. 118, No. 11, (Nov. 1971), pp.1851-1856	
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500	78	PUZANOV, N.I., et al., "Cultivation, Morphology and Structural Integrity of Dislocation-Free Silicon Tetracrystals", Inorganic Materials, Vol. 32, No. 8 (1996), pp. 903-912	X
501	79	PUZANOV, N.I., et al., "Harmful Microdefects in the Seed-End Portion of Large-Diameter Silicon Ingots", Inorganic Materials, Vol. 33, No. 8, (1997) pp. 765-769	
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535	82	ROKSNOER, P.J., "Microdefects in a Non-Striated Distribution in Floating-Zone Silicon Crystals", Journal of Crystal Growth, Vol. 53 (1981), pp. 563-573	
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535	84	SHIMANUKI, Y., et al., "Effects of Thermal History on Microdefect Formation in Czochralski Silicon Crystals", Japanese Journal of Applied Physics, Vol. 24, No. 12, (1985), pp. 1594-1599	
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535	86	SINNO, T., et al., "Point Defect Dynamics and the Oxidation-Induced Stacking-Fault Ring in Czochralski-Grown Silicon Crystals", J. Electrochem. Soc., Vol. 145, No. 1, (1998) pp. 302-318	
535	87	TAN, T. Y., "Point Defects, Diffusion Processes, and Swirl Defect Formation in Silicon", Appl. Phys. A., Vol. 37, (1985) pp. 1-17	
535	88	VANHELLEMONT, J., et al., "Defects in As-Grown Silicon and Their Evolution During Heat Treatments", Materials Science Forum, Vols. 258-263, (1997) pp. 341-346	
535	89	VORONKOV, V., "The Mechanism of Swirl Defects Formation in Silicon", Journal of Crystal Growth, Vol. 59 (1982) pp. 625-643.	

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SSS	90	VORONKOV, V., et al., "Behaviour and Effects of Intrinsic Point Defects in the Growth of Large Silicon Crystals", Electrochemical Society proceedings, Volume 97-22, (8/1997), pp. 3-17	
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SSS	93	ZIMMERMAN, H., et al. "Gold and Platinum Diffusion: the Key to the Understanding of Intrinsic Point Defect Behavior in Silicon", Applied Physics A Solids and Surfaces, Vol. A55, No. 1 (1992) pp. 121-134	
SSS	94	ZIMMERMAN, H., et al. "Vacancy concentration wafer mapping in silicon" Journal of Crystal Growth, Vol. 129, (1993) pp. 582-592.	

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